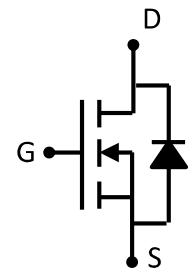


Feature

- 500V,3A
 $R_{DS(ON)} < 3.0 \Omega @ V_{GS}=10V$ TYP:2.6 Ω
- Fast Switching
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic diagram

Application

- PWM applications
- Load Switch
- Power management



TO-220F

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
3N50F	AP3N50F	TO-220F	-	-	1000

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ($T_a=25^\circ\text{C}$)	I_D	3	A
Continuous Drain Current ($T_a=100^\circ\text{C}$)	I_D	1.8	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	12	A
Single Pulsed Avalanche Energy ⁽²⁾	E_{AS}	45	mJ
Power Dissipation	P_D	25	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	4.9	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	500	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =500V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±30V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3.1	4	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =10V, I _D =1.5A	-	2.6	3.0	Ω
Forward tranconductance ⁽³⁾	g _{FS}	V _{DS} =10V, I _D =1.5A	0.5	-	-	S
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f =1MHz	-	278	-	pF
Output Capacitance	C _{oss}		-	20	-	
Reverse Transfer Capacitance	C _{rss}		-	5	-	
Switching characteristics						
Turn-off delay time	t _{d(off)}	V _{DD} =300V, I _D =3A, V _{GS} =10V, R _G =25Ω	-	13	-	ns
Total Gate Charge	Q _g	V _{DS} =480V, I _D =1A, V _{GS} =10V	-	4.8	-	nC
Gate-Source Charge	Q _{gs}		-	0.7	-	
Gate-Drain Charge	Q _{gd}		-	2.7	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V _{DS}	V _{GS} =0V, I _S =3A	-	-	1.4	V
Diode Forward current ⁽⁴⁾	I _S		-	-	3	A
Body Diode Reverse Recovery Time	t _{rr}	T _J =25° , IF=3A, di/dt=100A/us		190		ns
Body Diode Reverse Recovery Charge	Q _{rr}	T _J =25° , IF=3A, di/dt=100A/us		0.53		uc

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: T_J=25°C, V_{DD}=50V, R_G=2.0 Ω, L=10mH
3. Pulse Test: pulse width≤300μs, duty cycle≤2%
4. Surface Mounted on FR4 Board, t≤10 sec

Typical Characteristics

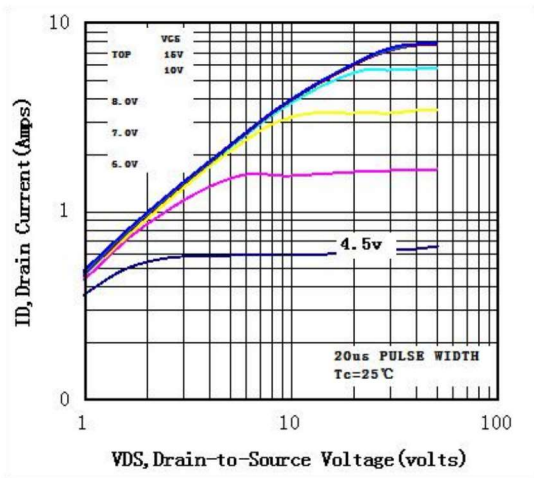


Fig1 Typical Output Characteristics, $T_c=25^\circ\text{C}$

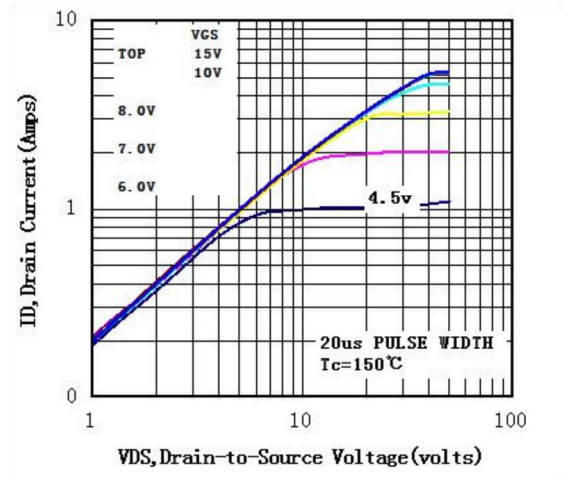


Fig2 Typical Output Characteristics, $T_c=150^\circ\text{C}$

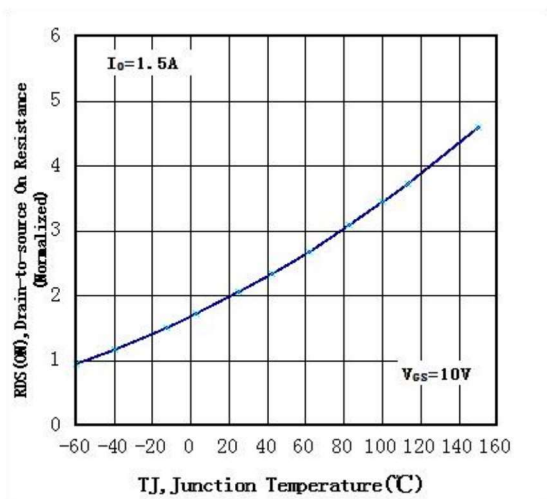


Fig3 Normalized On-Resistance Vs. Temperature

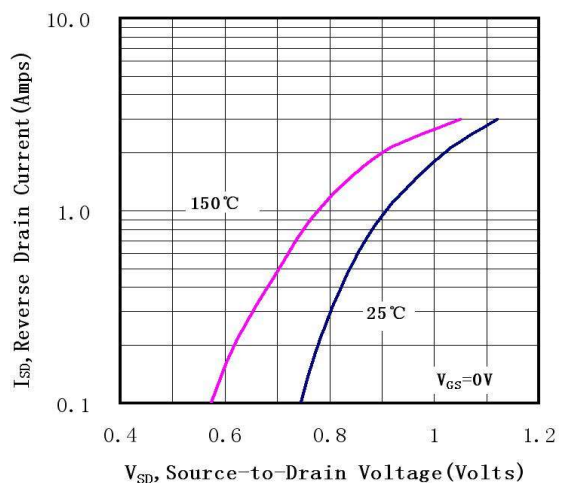


Fig4 Typical Source-Drain Diode Forward Voltage

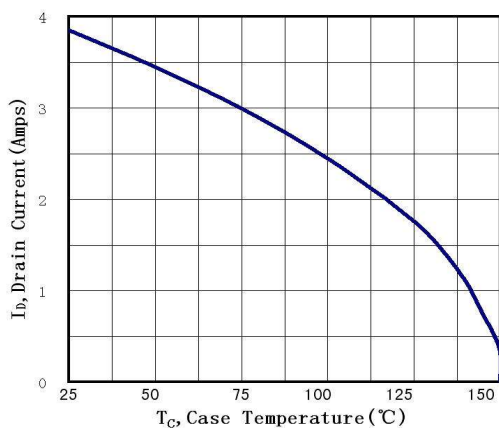


Fig5 Maximum Drain Current Vs. Case Temperature

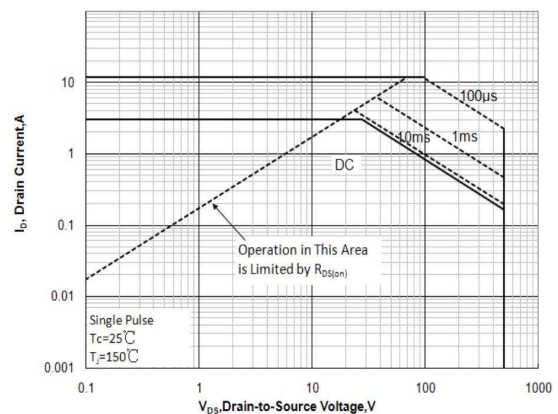
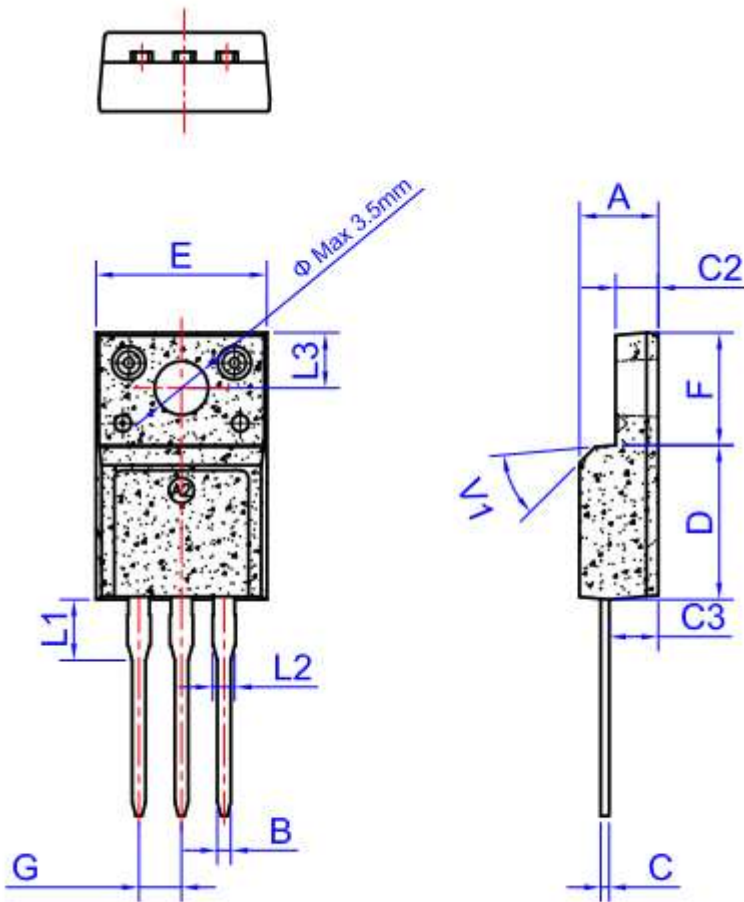


Fig6 Maximum Safe Operating Area

AP3N50F
N-Channel Power Mosfet

Package Outlines



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

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[MCQ7328-TP](#) [SSM3J143TU,LXHF](#) [DMN12M3UCA6-7](#) [PJMF280N65E1_T0_00201](#) [PJMF380N65E1_T0_00201](#)
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